

Silicon PNP Power Transistors

2N5954 2N5955 2N5956

DESCRIPTION

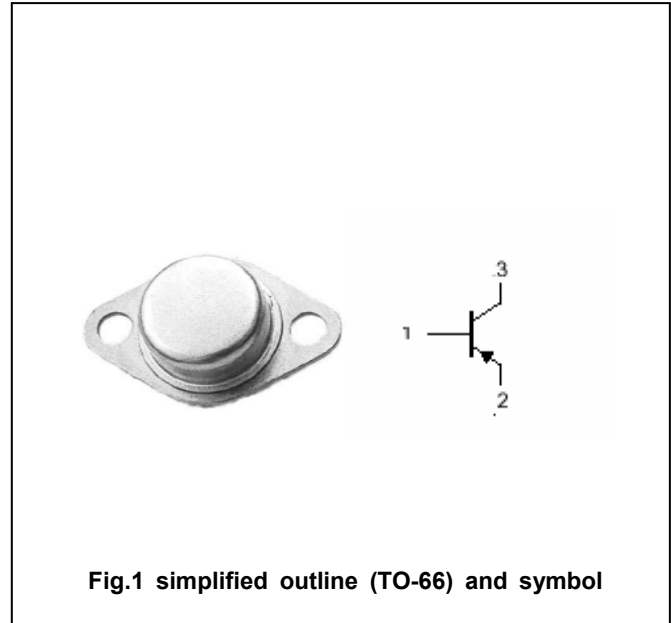
- With TO-66 package
- Low collector saturation voltage
- Excellent safe operating area
- Complement to type 2N6372/6373/6374

APPLICATIONS

- Designed for driver circuits, switching and amplifier applications

PINNING

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

Absolute maximum ratings($T_a = \square$)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	2N5954	-90	V
		2N5955	-70	
		2N5956	-50	
V_{CEO}	Collector-emitter voltage	2N5954	-80	V
		2N5955	-60	
		2N5956	-40	
V_{EBO}	Emitter-base voltage	Open collector	-5	V
I_C	Collector current		-6	A
I_B	Base current		-2	A
P_D	Total Power Dissipation	$T_C = 25 \square$	40	W
T_j	Junction temperature		150	\square
T_{stg}	Storage temperature		-65~200	\square

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	VALUE	UNIT
$R_{th\ j-c}$	Thermal resistance junction to case	4.3	\square/W

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CHARACTERISTICS

T_j=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CEO(SUS)}	Collector-emitter sustaining voltage	2N5954	-80			V
		2N5955	-60			
		2N5956	-40			
V _{CEsat}	Collector-emitter saturation voltage	2N5954				V
		2N5955			-1.0	
		2N5956				
V _{BE-1}	Base-emitter on voltage	2N5954				V
		2N5955			-2.0	
		2N5956				
V _{BE-2}	Base-emitter on voltage	I _C =-6A ; V _{CE} =-4V			-3.0	V
I _{CEO}	Collector cut-off current	2N5954				mA
		2N5955			-1.0	
		2N5956				
I _{CEV}	Collector cut-off current(R _{BE} =100Ω)	V _{CE} =Rated V _{CE} ; V _{BE(off)} =1.5V T _C =150°C			-0.1 -2.0	mA
I _{EBO}	Emitter cut-off current	V _{EB} =-5V; I _C =0			-0.1	mA
h _{FE-1}	DC current gain	2N5954				
		2N5955		20	100	
		2N5956				
h _{FE-2}	DC current gain	I _C =-6A ; V _{CE} =-4V	5			
f _T	Transition frequency	I _C =-1A;V _{CE} =-4V;f=1.0MHz	5			MHz

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PACKAGE OUTLINE



Fig.2 outline dimensions